



# BLY91C

## NPN SILICON RF POWER TRANSISTOR

### DESCRIPTION:

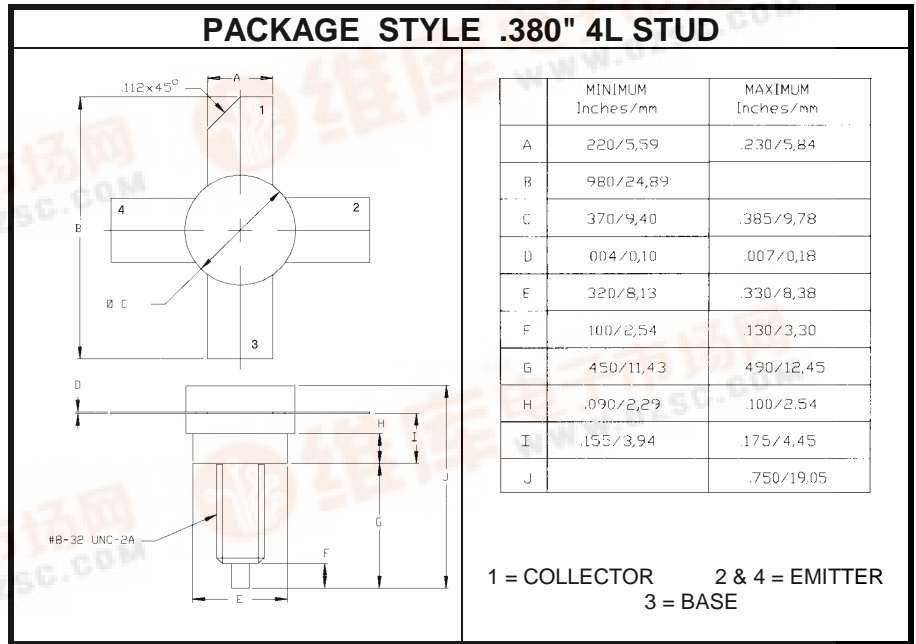
The **ASI BLY91C** is Designed for 28 V Large Signal Class A,B and C Amplifier Applications up to 175 MHz.

### FEATURES INCLUDE:

- Emitter Ballasting
- Gold Metalization
- 3/8" SOE Stud Package

### MAXIMUM RATINGS

$I_C$	1.0 A
$V_{CE}$	35 V
$V_{CB}$	65 V
$P_{DISS}$	20 W @ $T_C = 25^\circ C$
$T_J$	-65 °C to + 200 °C
$T_{STG}$	-65 °C to + 150 °C
$\theta_{JC}$	8.7 °C/W



### CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CES}$	$I_C = 200\text{ mA}$	65			V
$BV_{CEO}$	$I_C = 10\text{ mA}$	35			V
$BV_{EBO}$	$I_E = 1.0\text{ mA}$	4.0			V
$I_{CES}$	$V_{CE} = 36\text{ V}$			1.0	mA
$h_{FE}$	$V_{CE} = 5.0\text{ V}$ $I_C = 400\text{ mA}$	10		100	---
$C_{OB}$	$V_{CB} = 30\text{ V}$ $f = 1.0\text{ MHz}$			15	pF
$P_G$	$V_{CC} = 28\text{ V}$ $P_{OUT} = 8.0\text{ W}$ $f = 175\text{ MHz}$	12.0	13.0		dB
$\eta_c$		65			%

